



Weebit Nano's first phase electrical results validate the potential of its ReRAM SiOx memory technology

On track to miniaturisation target of 40nm by the end of 2017

23 March, 2017 – [Weebit Nano Ltd](#) [ASX: WBT] is pleased to announce the successful electrical results of its Silicon Oxide (SiOx) ReRAM technology. These electrical results followed extensive measurements on critical memory parameters, such as programming and erase voltage, as well as current levels. These successful results, achieved in Leti's pre-industrialisation cleanroom, are a significant step forward in confirming the memory behaviour of Weebit Nano's proprietary ReRAM SiOx technology. The company is now able to move forward with scaling down its technology to seek to achieve its miniaturisation target of 40nm.

Yossi Keret, CEO of Weebit Nano, said: "We are very pleased with the results achieved with our technology partner, Leti. These results represent a significant milestone for us and are a testament to our productive partnership with Leti. We are now able to move forward with our mid-term plans of scaling down our ReRAM technology towards the miniaturisation target of 40nm. The achievement of this target will bring us closer to commercialisation.

"Weebit Nano is at the forefront of creating an exciting technology evolution. With world memory storage use growing exponentially, our technology development is seeking to offer a solution to a market that is currently estimated at over US\$37 billion. We look forward to continuing our development program as we seek to create the next generation in emerging memory", said Mr. Keret.

In addition to the announced electrical results, Weebit Nano is further characterising its ReRAM technology with Leti in order to upgrade the manufacturability of the technology towards a commercially viable product. The next stage of development will utilise Leti's exclusive Memory Advanced Demonstrator vehicle, which is a fully integrated chip that includes all the components a real memory device requires, such as memory arrays, CMOS logic and interconnects.



The Memory Advanced Demonstrator vehicle chip development is on track to enable scaling of the technology towards the miniaturisation target of 40nm by the end of this year, consistent with the previously announced timeline. Achieving the miniaturisation target of 40nm will be a significant technical milestone to allow commercial collaboration with key players in the industry, which includes possible licensing opportunities.

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About Weebit Nano Limited

Weebit Nano is an exciting venture that is leading the way into the future of computer memory storage, and plans to become the new industry standard in this space.

Incorporated in Israel in 2015, Weebit was built to address the growing need for data storage technology around a revolutionary memory technology. Weebit has secured several patents to ensure optimal commercial and legal protection for its ground-breaking technology.

This quantum leap will allow semiconductor memory elements to become cheaper, faster, more reliable and more energy efficient than the existing Flash technology. Weebit has signed an R&D agreement with Leti, an R&D institute that specialises in nanotechnologies, to further develop SiOx ReRAM technology. For more information please visit: <http://www.weebit-nano.com/>

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